

SuperMOS - TO-252 -40V  $BV_{DSS}$ ,  $13m\Omega$   $R_{DS(on)}$ , P-channel MOSFET

## 1. Description

The ESD4185 is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent  $R_{DS(on)}$  with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESD4185 is Pb-free.

## 2. Features

- -40V,  $R_{DS(on)}=13m\Omega$ (TYP.) @ $V_{GS}=-10V$   
 $R_{DS(on)}=17m\Omega$ (TYP.) @ $V_{GS}=-4.5V$
- Fast Switching
- High density cell design for low  $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

## 3. Applications

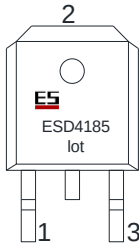
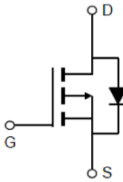
- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED!

## 4. Ordering Information

| Part Number | Package | Marking     | Material     | Packing     | Quantity per reel | Flammability Rating | Reel size |
|-------------|---------|-------------|--------------|-------------|-------------------|---------------------|-----------|
| ESD4185     | TO-252  | ESD4185/lot | Halogen free | Tape & Reel | 2,500 PCS         | UL 94V-0            | 13 inches |

## 5. Pin Configuration and Functions

| Pin | Function | Outline                                                                             | Circuit Diagram                                                                       |
|-----|----------|-------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| 1   | Gate     |  |  |
| 3   | Source   |                                                                                     |                                                                                       |
| 2   | Drain    |                                                                                     |                                                                                       |

## 6. Specification

### Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

| Parameter                                     |                   | Symbol     | Limit       | Unit |
|-----------------------------------------------|-------------------|------------|-------------|------|
| Drain-Source Voltage                          |                   | $BV_{DSS}$ | -40         | V    |
| Gate-Source Voltage                           |                   | $V_{GS}$   | ±25         | V    |
| Continuous Drain Current                      | $T_C=25^{\circ}C$ | $I_D$      | -45         | A    |
|                                               | $T_C=75^{\circ}C$ |            | -34         |      |
| Maximum Power Dissipation                     | $T_C=25^{\circ}C$ | $P_D$      | 52          | W    |
|                                               | $T_C=75^{\circ}C$ |            | 32          |      |
| Pulsed Drain Current <sup>a</sup>             |                   | $I_{DM}$   | -180        | A    |
| Avalanche Current, Single Pulsed <sup>b</sup> |                   | $I_{AS}$   | 33          | A    |
| Avalanche Energy, Single Pulsed <sup>b</sup>  |                   | $E_{AS}$   | 163         | mJ   |
| Operating Junction Temperature                |                   | $T_J$      | 150         | °C   |
| Storage Temperature Range                     |                   | $T_{stg}$  | -55 to +150 | °C   |

### Thermal resistance ratings

| Single Operation                       |                      |                 |     |     |      |
|----------------------------------------|----------------------|-----------------|-----|-----|------|
| Parameter                              |                      | Symbol          | Typ | Max | Unit |
| Junction-to-Ambient Thermal Resistance | $t \leq 10\text{ s}$ | $R_{\theta JA}$ | 15  | 20  | °C/W |
| Junction-to-Case Thermal Resistance    | Steady State         | $R_{\theta JC}$ | 2   | 2.4 |      |

Note:

a: Repetitive rating, pulse width limited by junction temperature,  $t_p=10\mu\text{s}$ , Duty Cycle=1%

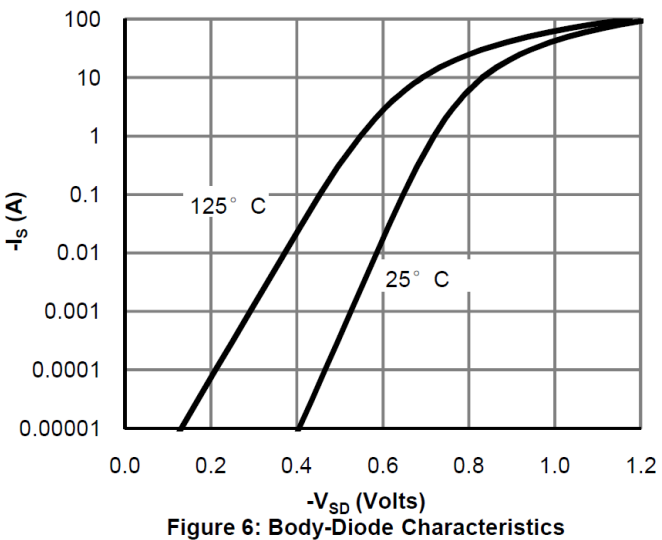
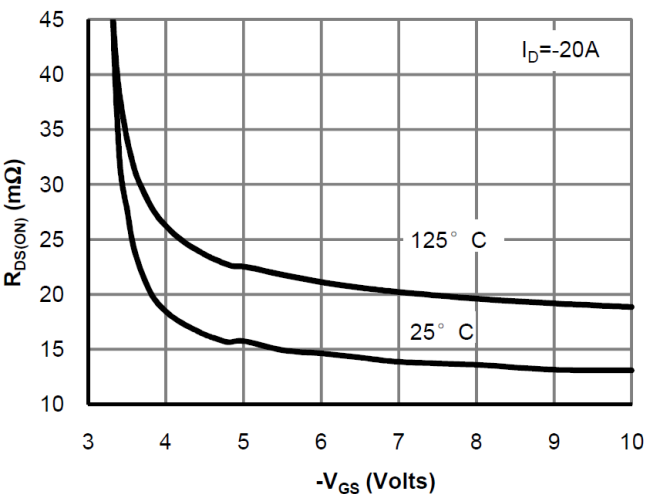
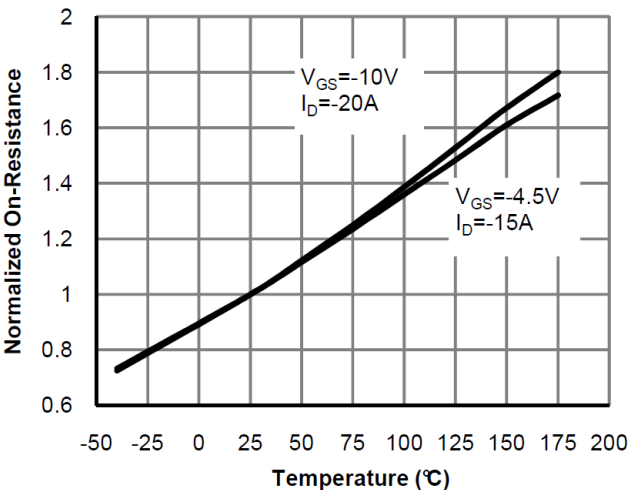
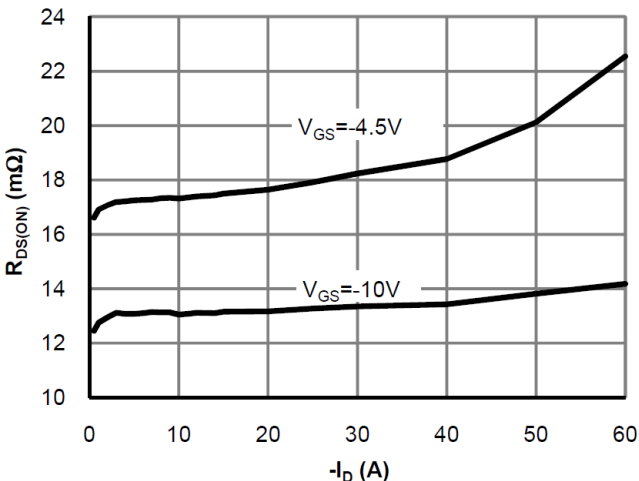
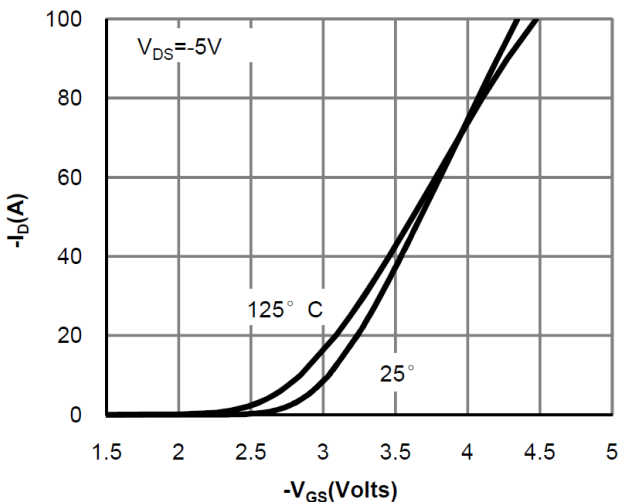
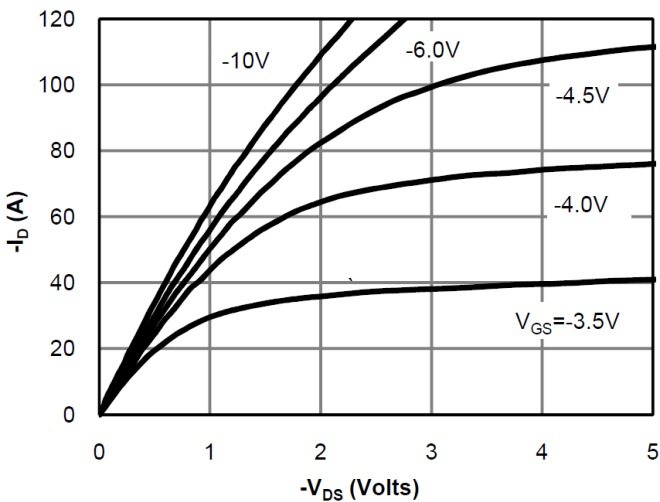
b: EAS condition:  $T_J=25^{\circ}C$ ,  $V_{DD}=-30V$ ,  $V_G=-10V$ ,  $L=0.3mH$ ,  $R_g=25\Omega$

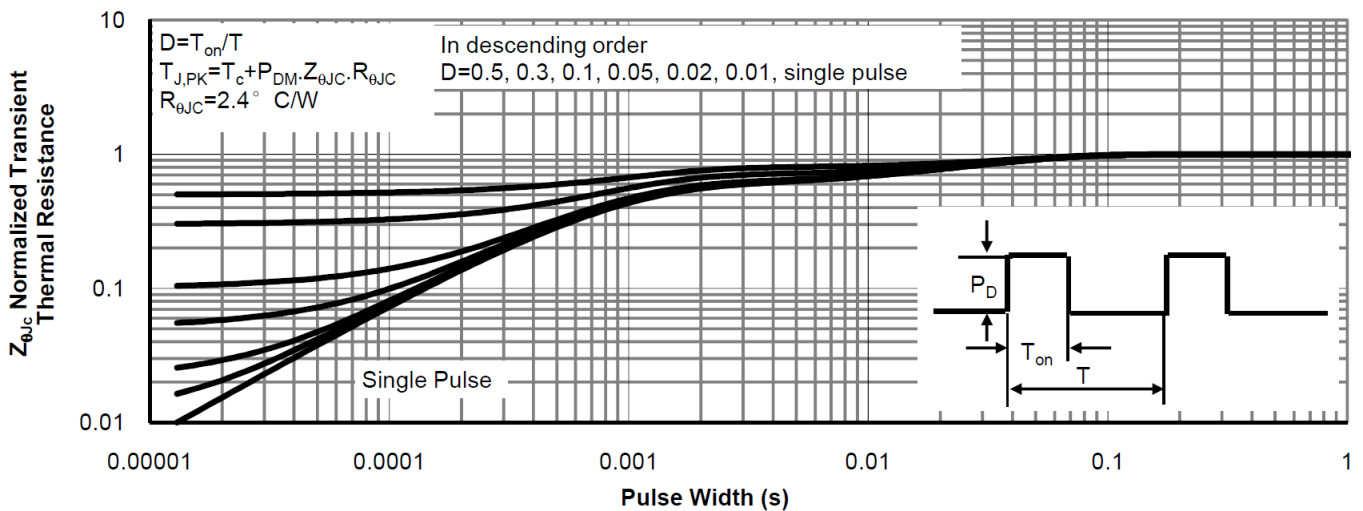
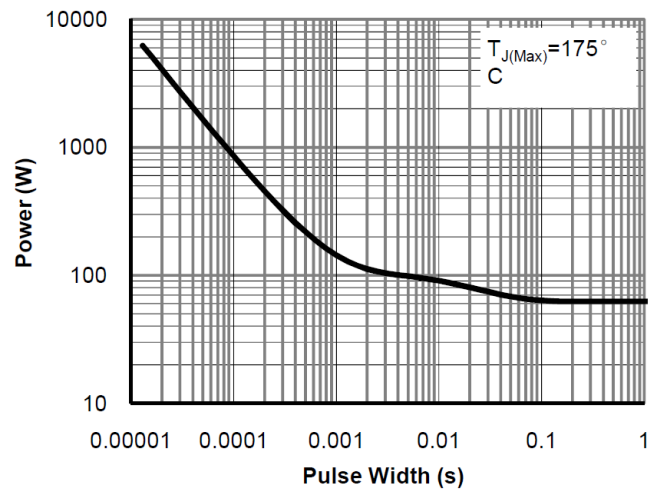
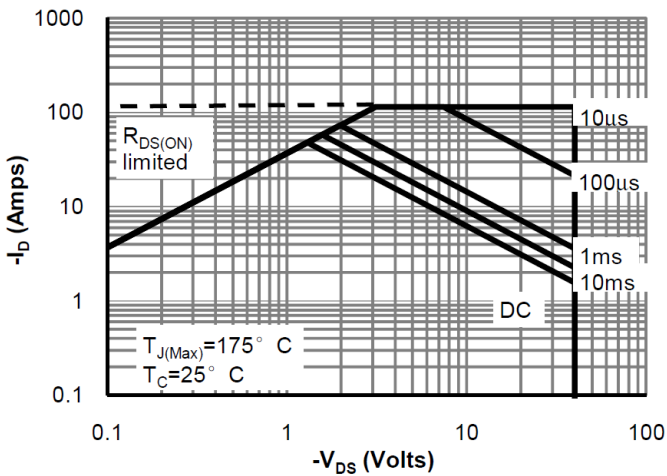
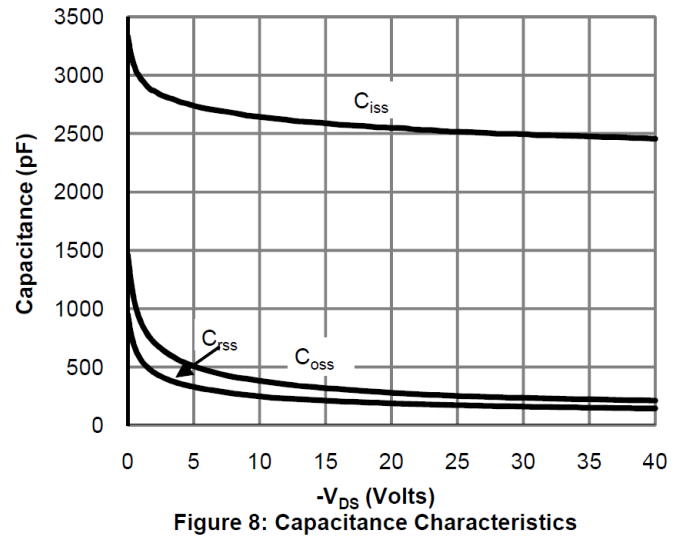
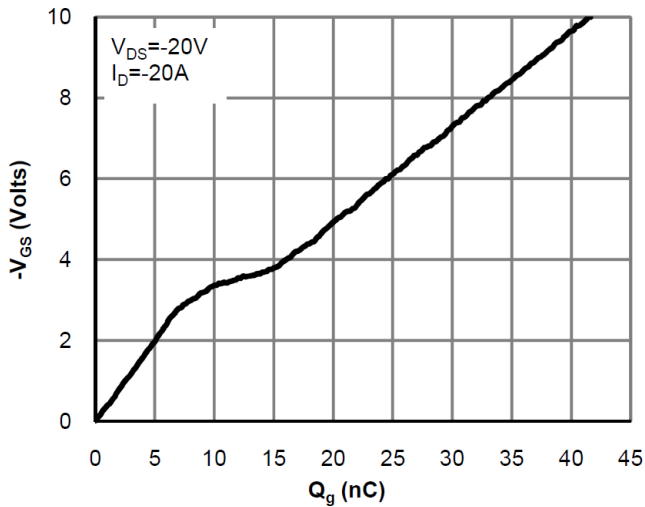
## Electrical Characteristics

At TA = 25°C unless otherwise specified

| Parameter                                 | Symbol              | Test Conditions                                                                      | Min. | Typ. | Max. | Unit |
|-------------------------------------------|---------------------|--------------------------------------------------------------------------------------|------|------|------|------|
| OFF CHARACTERISTICS                       |                     |                                                                                      |      |      |      |      |
| Drain-to-Source Breakdown Voltage         | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA                                          | -40  |      |      | V    |
| Zero Gate Voltage Drain Current           | I <sub>DSS</sub>    | V <sub>GS</sub> =0V, V <sub>DS</sub> =-40V                                           |      |      | -1   | uA   |
| Gate-to-source Leakage Current            | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                                           |      |      | ±100 | nA   |
| ON CHARACTERISTICS                        |                     |                                                                                      |      |      |      |      |
| Gate Threshold Voltage                    | V <sub>GS(TH)</sub> | V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA                            | -1.0 | -1.6 | -2.0 | V    |
| Drain-to-source On-resistance             | R <sub>DS(on)</sub> | V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A                                          |      | 13   | 16   | mΩ   |
|                                           |                     | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-15A                                         |      | 17   | 20   |      |
| CHARGES, CAPACITANCES AND GATE RESISTANCE |                     |                                                                                      |      |      |      |      |
| Input Capacitance                         | C <sub>ISS</sub>    | V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz                                   |      | 2500 |      | pF   |
| Output Capacitance                        | C <sub>OSS</sub>    |                                                                                      |      | 260  |      |      |
| Reverse Transfer Capacitance              | C <sub>RSS</sub>    |                                                                                      |      | 180  |      |      |
| Total Gate Charge                         | Q <sub>G(TOT)</sub> | V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-20A                   |      | 42   |      | nC   |
| Gate-to-Source Charge                     | Q <sub>GS</sub>     |                                                                                      |      | 7    |      |      |
| Gate-to-Drain Charge                      | Q <sub>GD</sub>     |                                                                                      |      | 8.8  |      |      |
| SWITCHING CHARACTERISTICS                 |                     |                                                                                      |      |      |      |      |
| Turn-On Delay Time                        | t <sub>d(ON)</sub>  | V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =1Ω, R <sub>G</sub> =3Ω |      | 10   |      | ns   |
| Rise Time                                 | t <sub>r</sub>      |                                                                                      |      | 20   |      |      |
| Turn-Off Delay Time                       | t <sub>d(OFF)</sub> |                                                                                      |      | 55   |      |      |
| Fall Time                                 | t <sub>f</sub>      |                                                                                      |      | 30   |      |      |
| BODY DIODE CHARACTERISTICS                |                     |                                                                                      |      |      |      |      |
| Forward Voltage                           | V <sub>SD</sub>     | V <sub>GS</sub> =0V, I <sub>SD</sub> =-1A                                            |      | -0.7 | -1.2 | V    |

7. Typical Characteristic







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